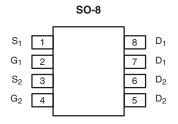


Dual P-Channel 20V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
	0.018 at V _{GS} = - 4.5 V	- 8.9		
- 20	0.022 at V _{GS} = - 2.5 V	- 8.1		
	0.030 at V _{GS} = - 1.8 V	- 3.6		



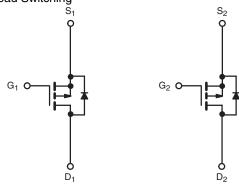
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC

ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

Load Switching



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		V
Continuous Drain Current /T 150 °C\a	T _A = 25 °C	I _D	- 8.9	- 6.7	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 7.1	- 5.4	
Pulsed Drain Current		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9	
Mariana Brasila di ad	T _A = 25 °C	P _D	2.0	1.1	W
Maximum Power Dissipation ^a	T _A = 70 °C	T D	1.3	0.7] **
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestore bounding to Austriant	t ≤ 10 s	R _{thJA}	46	62.5	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	80	110	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	24	32	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



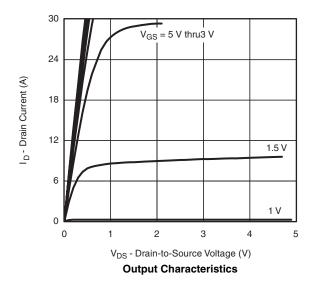
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static				•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -350 \mu A$	- 0.4		- 1.0	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zava Cata Valta da Busin Comunat		V _{DS} = - 20 V, V _{GS} = 0 V			- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μΑ
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 30			Α
		V _{GS} = - 4.5 V, I _D = - 8.9 A		0.018		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 8.1 A	s = - 2.5 V, I _D = - 8.1 A			Ω
		V _{GS} = - 1.8 V, I _D = - 3.6 A		0.030		1
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 8.9 A		26		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.7	- 1.2	V
Dynamic ^b						
Total Gate Charge	Q_g			34.5	52	
Gate-Source Charge	Q_{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 8.9 A		5.1		nC
Gate-Drain Charge	Q_{gd}			9.6		
Gate Resistance	R_g			9		Ω
Turn-On Delay Time	t _{d(on)}			25	40	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 6 Ω		46	70	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		230	345	ns
Fall Time	t _f			155	235	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		128	200	

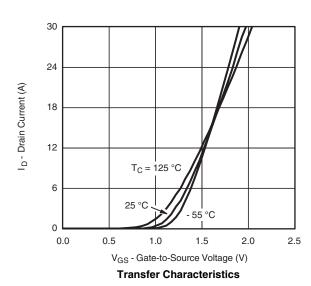
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

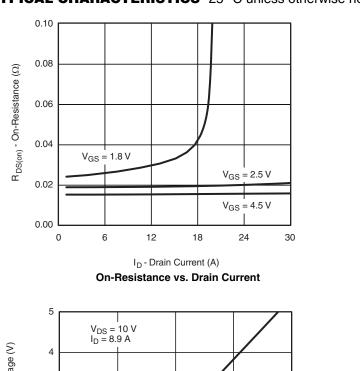
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

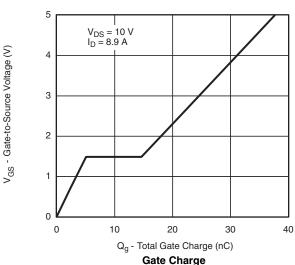


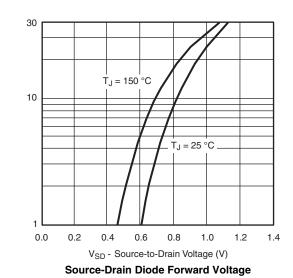


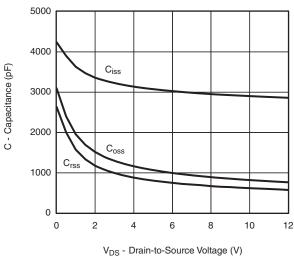


TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

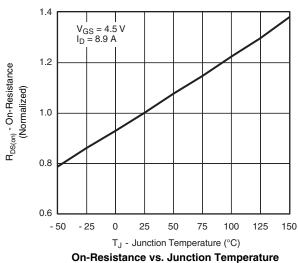


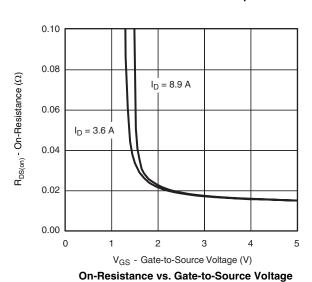






Capacitance



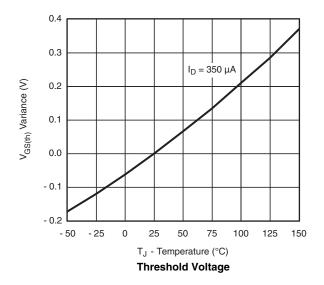


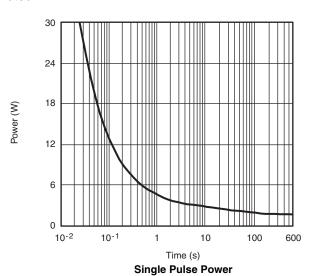
服务热线:400-655-8788

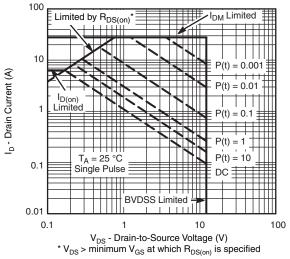
Is - Source Current (A)



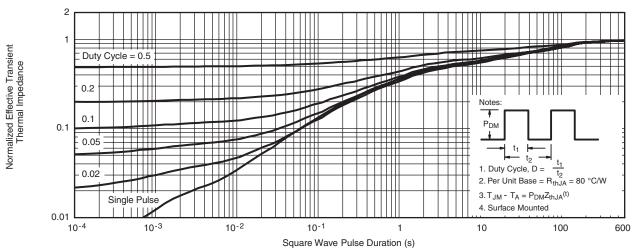
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted







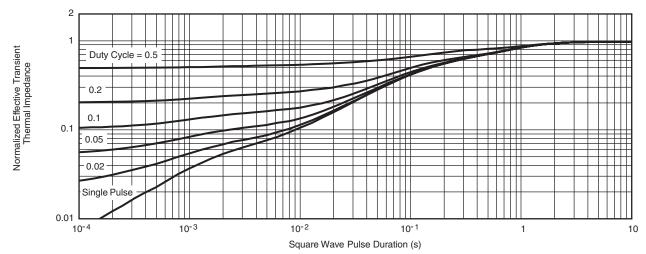
Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



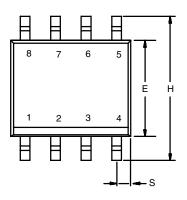
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

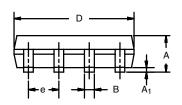


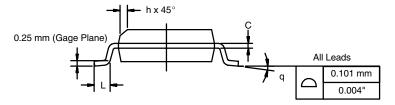
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEADJEDEC Part Number: MS-012





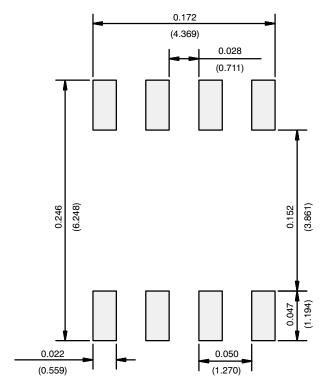


	MILLIMETERS INCHES			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06						

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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